2SD1620



http://onsemi.com

Bipolar Transistor 10V, 3A, Low VCE(sat), NPN Single PCP

Features

- · Less power dissipation because of low VCE(sat), permitting more flashes of light to be emitted
- · Large current capacity and highly resistant to breakdown
- Excellent linearity of hFE in the region from low current to high current
- · Ultrasmall size supports high-density, ultrasmall-sized hybrid IC designs

Specifications

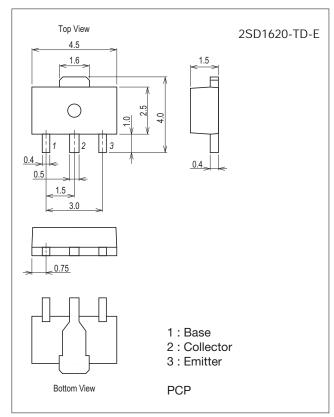
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		30	V
Collector-to-Emitter Voltage	VCEX		20	V
Collector-to-Emitter Voltage	VCEO		10	V
Emitter-to-Base Voltage	VEBO		6	V
Collector Current	IC		3	А
Collector Current (Pulse)	ICP		5	А

Continued on next page.

Package Dimensions

unit : mm (typ) 7007B-004



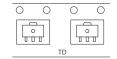
Product & Package Information

• Package : PCP

• JEITA, JEDEC : SC-62, SOT-89, TO-243

• Minimum Packing Quantity: 1,000 pcs./reel

Packing Type: TD Marking





Electrical Connection



Continued from preceding page.

Parameter	Symbol	Conditions	Ratings	Unit
Collector Dissipation	PC		500	mW
		When mounted on ceramic substrate (250mm ² x0.8mm)	1.3	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

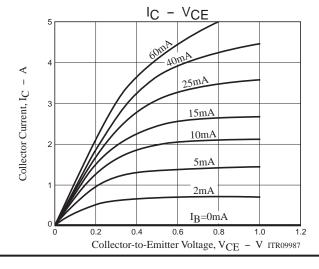
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

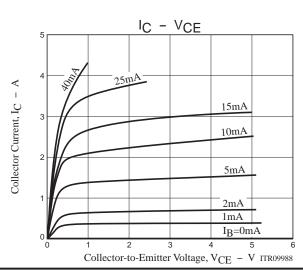
Electrical Characteristics at Ta=25°C

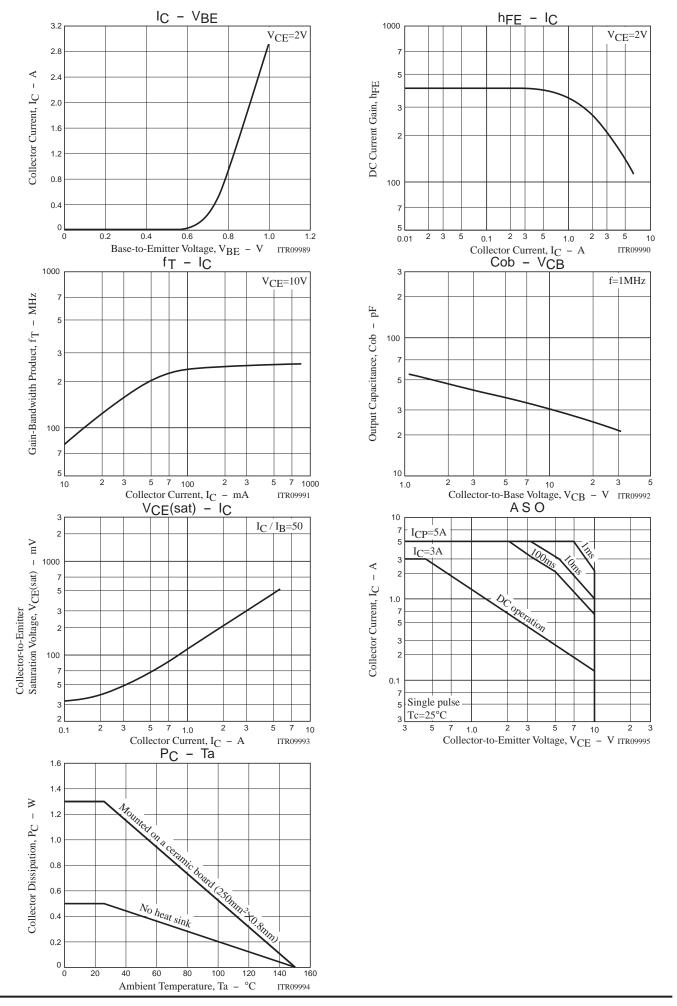
Parameter	Symbol	Conditions Ratings min typ max			Unit	
	Syllibol			typ	max	Office
Collector Cutoff Current	ICBO	V _{CB} =20V, I _E =0A			100	nA
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0A			100	nA
DC Current Gain	hFE	V _{CE} =2V, I _C =3A	140	210		
Gain-Bandwidth Product	fŢ	V _{CE} =10V, I _C =50mA		200		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		30		pF
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	IC=3A, IB=60mA		0.3	0.4	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =10μA, I _E =0A	30			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEX	I _C =1mA, V _{BE} =3V	20			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	10			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0A	6			V

Ordering Information

Device	Package	Shipping	memo	
2SD1620-TD-E	PCP	1,000pcs./reel	Pb Free	





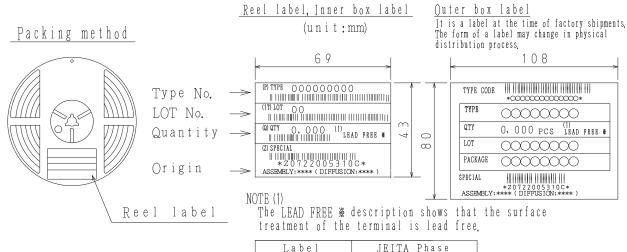


Bag Packing Specification

2SD1620-TD-E

1. Packing Format

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)		
PCP	PCP	1, 000	4,000	24,000	4 reels contained	6 inner boxes contained		
					Dimensions:mm (external)	Dimensions:mm (external)		
					183×72×185	440×195×210		



LEAD FREE 3

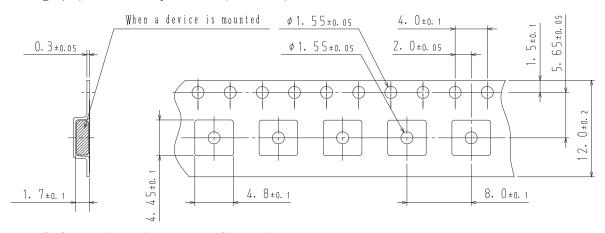
LEAD FREE 4

JEITA Phase 3A

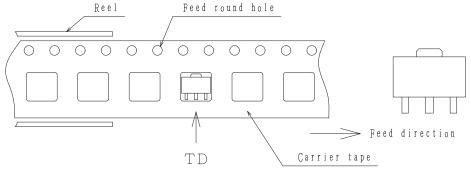
JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



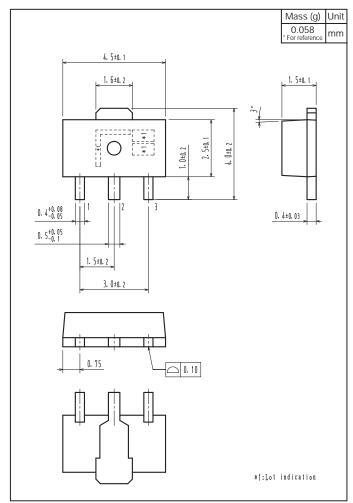
2-2. Device placement direction



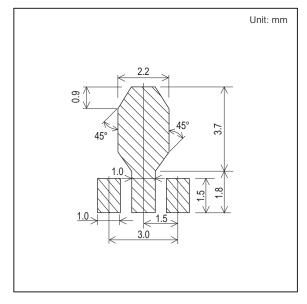
Those with pin 1 index on the feed hole side·····TD

Outline Drawing

2SD1620-TD-E



Land Pattern Example



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